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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, DCMI, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f417vet6

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Figure 5 shows the general block diagram of the device family.

Table 2. STM32F415xx and STM32F417xx: features and peripheral counts

Peripherals		STM32F415RG	STM32F415OG	STM32F415VG	STM32F415ZG	STM32F417Vx		STM32F417Zx		STM32F417Ix	
Flash memory in Kbytes		1024				512	1024	512	1024	512	1024
SRAM in Kbytes	System	192(112+16+64)									
	Backup	4									
FSMC memory controller		No	Yes ⁽¹⁾								
Ethernet		No				Yes					
Timers	General-purpose	10									
	Advanced-control	2									
	Basic	2									
	IWDG	Yes									
	WWDG	Yes									
	RTC	Yes									
Random number generator		Yes									
Communication interfaces	SPI / I ² S	3/2 (full duplex) ⁽²⁾									
	I ² C	3									
	USART/UART	4/2									
	USB OTG FS	Yes									
	USB OTG HS	Yes									
	CAN	2									
	SDIO	Yes									
Camera interface		No				Yes					
Cryptography		Yes									

2.1 Full compatibility throughout the family

The STM32F415xx and STM32F417xx are part of the STM32F4 family. They are fully pin-to-pin, software and feature compatible with the STM32F2xx devices, allowing the user to try different memory densities, peripherals, and performances (FPU, higher frequency) for a greater degree of freedom during the development cycle.

The STM32F415xx and STM32F417xx devices maintain a close compatibility with the whole STM32F10xxx family. All functional pins are pin-to-pin compatible. The STM32F415xx and STM32F417xx, however, are not drop-in replacements for the STM32F10xxx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xxx to the STM32F41xxx family remains simple as only a few pins are impacted.

[Figure 4](#), [Figure 3](#), [Figure 2](#), and [Figure 1](#) give compatible board designs between the STM32F41xxx, STM32F2, and STM32F10xxx families.

Figure 1. Compatible board design between STM32F10xx/STM32F41xxx for LQFP64

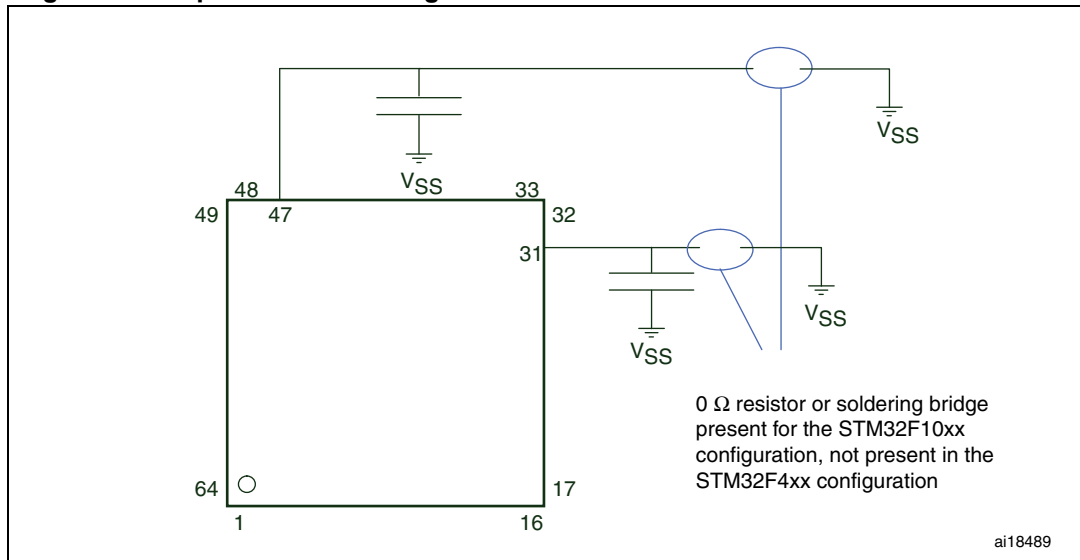
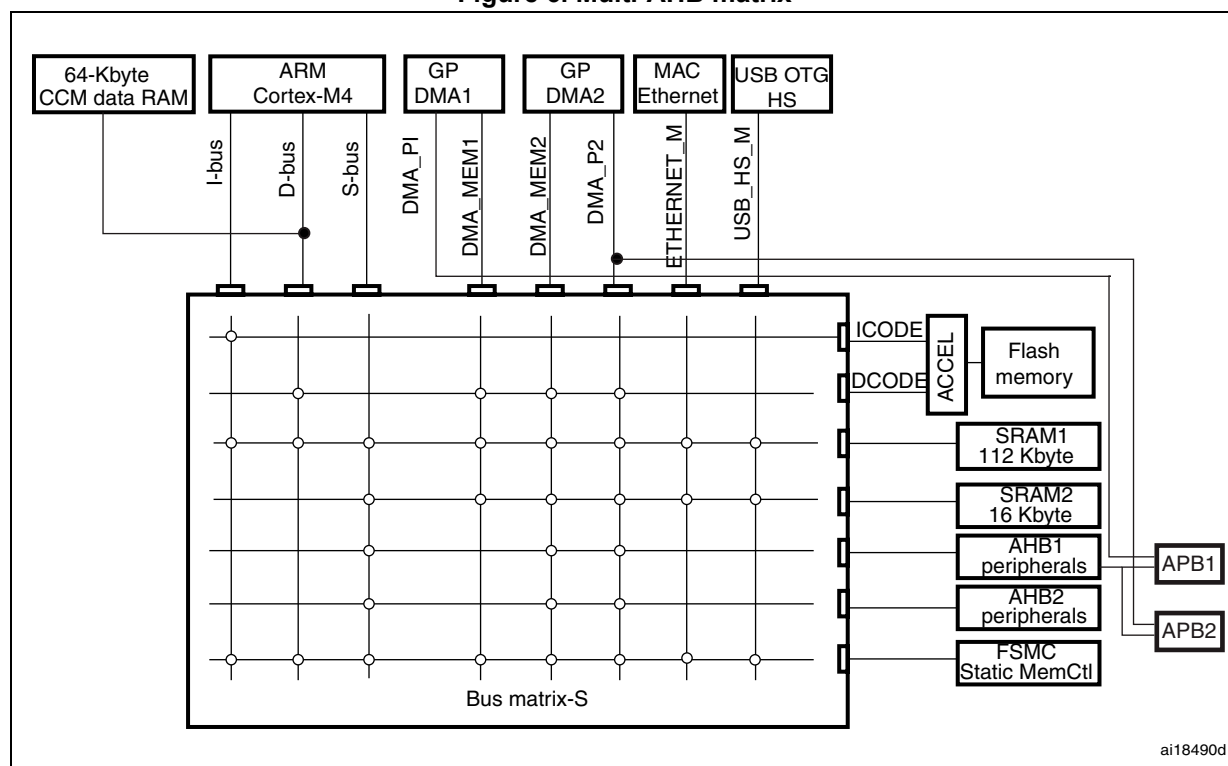


Figure 6. Multi-AHB matrix



2.2.8 DMA controller (DMA)

The devices feature two general-purpose dual-port DMAs (DMA1 and DMA2) with 8 streams each. They are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. They feature dedicated FIFOs for APB/AHB peripherals, support burst transfer and are designed to provide the maximum peripheral bandwidth (AHB/APB).

The two DMA controllers support circular buffer management, so that no specific code is needed when the controller reaches the end of the buffer. The two DMA controllers also have a double buffering feature, which automates the use and switching of two memory buffers without requiring any special code.

Each stream is connected to dedicated hardware DMA requests, with support for software trigger on each stream. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals:

- SPI and I²S
- I²C
- USART
- General-purpose, basic and advanced-control timers TIMx
- DAC
- SDIO
- Cryptographic acceleration
- Camera interface (DCMI)
- ADC.

2.2.9 Flexible static memory controller (FSMC)

The FSMC is embedded in the STM32F415xx and STM32F417xx family. It has four Chip Select outputs supporting the following modes: PCCard/Compact Flash, SRAM, PSRAM, NOR Flash and NAND Flash.

Functionality overview:

- Write FIFO
- Maximum FSMC_CLK frequency for synchronous accesses is 60 MHz.

LCD parallel interface

The FSMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

2.2.10 Nested vectored interrupt controller (NVIC)

The STM32F415xx and STM32F417xx embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 82 maskable interrupt channels plus the 16 interrupt lines of the Cortex[®]-M4 with FPU core.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving, higher-priority interrupts
- Support tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimum interrupt latency.

SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

2.2.22 Inter-integrated circuit interface (I²C)

Up to three I²C bus interfaces can operate in multimaster and slave modes. They can support the Standard-mode (up to 100 kHz) and Fast-mode (up to 400 kHz). They support the 7/10-bit addressing mode and the 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

2.2.23 Universal synchronous/asynchronous receiver transmitters (USART)

The STM32F415xx and STM32F417xx embed four universal synchronous/asynchronous receiver transmitters (USART1, USART2, USART3 and USART6) and two universal asynchronous receiver transmitters (UART4 and UART5).

These six interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART1 and USART6 interfaces are able to communicate at speeds of up to 10.5 Mbit/s. The other available interfaces communicate at up to 5.25 Mbit/s.

USART1, USART2, USART3 and USART6 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.

Table 7. STM32F41xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
33	J3	51	73	P12	92	PB12	I/O	FT	-	SPI2_NSS / I2S2_WS / I2C2_SMBA/ USART3_CK/ TIM1_BKIN / CAN2_RX / OTG_HS_ULPI_D5/ ETH_RMII_TXD0 / ETH_MII_TXD0/ OTG_HS_ID/ EVENTOUT	-
34	J1	52	74	P13	93	PB13	I/O	FT	-	SPI2_SCK / I2S2_CK / USART3_CTS/ TIM1_CH1N /CAN2_TX / OTG_HS_ULPI_D6 / ETH_RMII_TXD1 / ETH_MII_TXD1/ EVENTOUT	OTG_HS_VBUS
35	J2	53	75	R14	94	PB14	I/O	FT	-	SPI2_MISO/ TIM1_CH2N / TIM12_CH1 / OTG_HS_DM/ USART3_RTS / TIM8_CH2N/I2S2ext_SD/ EVENTOUT	-
36	H1	54	76	R15	95	PB15	I/O	FT	-	SPI2_MOSI / I2S2_SD/ TIM1_CH3N / TIM8_CH3N / TIM12_CH2 / OTG_HS_DP/ EVENTOUT	RTC_REFIN
-	H2	55	77	P15	96	PD8	I/O	FT	-	FSMC_D13 / USART3_TX/ EVENTOUT	-
-	H3	56	78	P14	97	PD9	I/O	FT	-	FSMC_D14 / USART3_RX/ EVENTOUT	-
-	G3	57	79	N15	98	PD10	I/O	FT	-	FSMC_D15 / USART3_CK/ EVENTOUT	-
-	G1	58	80	N14	99	PD11	I/O	FT	-	FSMC_CLE / FSMC_A16/USART3_CTS/ EVENTOUT	-
-	G2	59	81	N13	100	PD12	I/O	FT	-	FSMC_ALE/ FSMC_A17/TIM4_CH1 / USART3_RTS/ EVENTOUT	-

Table 28. Peripheral current consumption (continued)

Peripheral		I _{DD} (Typ) ⁽¹⁾		Unit
		Scale1 (up to 168 MHz)	Scale2 (up to 144 MHz)	
AHB2 (up to 168 MHz)	OTG_FS	26.45	26.67	μA/MHz
	DCMI	5.87	5.35	
	RNG	1.50	1.67	
	Hash	9.73	8.86	
	Crypto	2.23	2.08	
AHB3 (up to 168 MHz)	FSMC	12.46	11.31	μA/MHz
Bus matrix ⁽²⁾		13.10	11.81	μA/MHz

Table 28. Peripheral current consumption (continued)

Peripheral		I _{DD} (Typ) ⁽¹⁾		Unit
		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	
APB1 (up to 42 MHz)	TIM2	16.71	16.50	μA/MHz
	TIM3	12.33	11.94	
	TIM4	13.45	12.92	
	TIM5	17.14	16.58	
	TIM6	2.43	3.06	
	TIM7	2.43	2.22	
	TIM12	6.62	6.83	
	TIM13	5.05	5.47	
	TIM14	5.26	5.61	
	PWR	1.00	0.56	
	USART2	2.69	2.78	
	USART3	2.74	2.78	
	UART4	3.24	3.33	
	UART5	2.69	2.78	
	I2C1	2.67	2.50	
	I2C2	2.83	2.78	
	I2C3	2.81	2.78	
	SPI2	2.43	2.22	
	SPI3	2.43	2.22	
	I2S2 ⁽³⁾	2.43	2.22	
	I2S3 ⁽³⁾	2.26	2.22	
	CAN1	5.12	5.56	
	CAN2	4.81	5.28	
	DAC ⁽⁴⁾	1.67	1.67	
	WWDG	1.00	0.83	

Low-speed external user clock generated from an external source

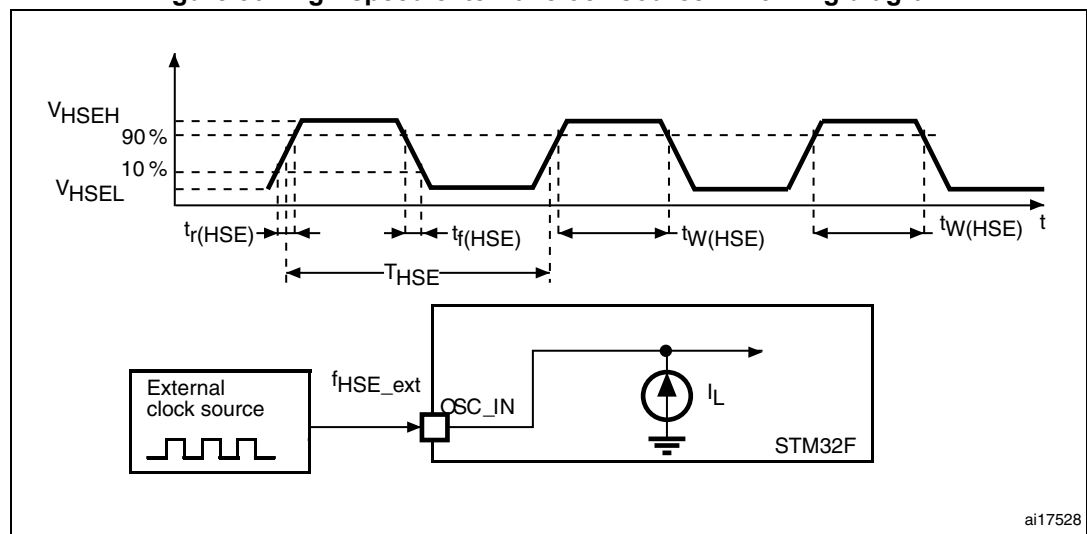
The characteristics given in [Table 31](#) result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 14](#).

Table 31. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency ⁽¹⁾	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance ⁽¹⁾	-	-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design.

Figure 30. High-speed external clock source AC timing diagram



Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC² code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 44. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{CPU}]	Unit
				25/168 MHz	
S _{EMI}	Peak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running from Flash with ART accelerator enabled	0.1 to 30 MHz	32	dBμV
			30 to 130 MHz	25	
			130 MHz to 1GHz	29	
			SAE EMI Level	4	-
		V _{DD} = 3.3 V, T _A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, code running from Flash with ART accelerator and PLL spread spectrum enabled	0.1 to 30 MHz	19	dBμV
			30 to 130 MHz	16	
			130 MHz to 1GHz	18	
			SAE EMI level	3.5	-

5.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 45. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C conforming to JESD22-A114	2	2000 ⁽²⁾	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C conforming to ANSI/ESD STM5.3.1	II	500	

1. Guaranteed by characterization.

2. On V_{BAT} pin, V_{ESD(HBM)} is limited to 1000 V.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 46. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

5.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in [Table 47](#).

Table 48. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
V _{HYS}	FT, TTa and NRST I/O input hysteresis		1.7 V ≤V _{DD} ≤3.6 V	10%V _{DD} ⁽³⁾	-	-	V
	BOOT0 I/O input hysteresis		1.75 V ≤V _{DD} ≤3.6 V -40 °C≤T _A ≤105 °C	0.1	-	-	
			1.7 V ≤V _{DD} ≤3.6 V 0 °C≤T _A ≤105 °C				
I _{lkg}	I/O input leakage current ⁽⁴⁾		V _{SS} ≤V _{IN} ≤V _{DD}	-	-	±1	μA
	I/O FT input leakage current ⁽⁵⁾		V _{IN} = 5 V	-	-	3	
R _{PU}	Weak pull-up equivalent resistor ⁽⁶⁾	All pins except for PA10 and PB12 (OTG_FS_ID, OTG_HS_ID)	V _{IN} = V _{SS}	30	40	50	kΩ
		PA10 and PB12 (OTG_FS_ID, OTG_HS_ID)	-	7	10	14	
R _{PD}	Weak pull-down equivalent resistor ⁽⁷⁾	All pins except for PA10 and PB12	V _{IN} = V _{DD}	30	40	50	
		PA10 and PB12	-	7	10	14	
C _{IO} ⁽⁸⁾	I/O pin capacitance			-	5	-	pF

1. Guaranteed by design.
2. Tested in production.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 47: I/O current injection susceptibility](#)
5. To sustain a voltage higher than $V_{DD} + 0.3\text{ V}$, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins. Refer to [Table 47: I/O current injection susceptibility](#).
6. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters.

5.3.18 TIM timer characteristics

The parameters given in [Table 52](#) and [Table 53](#) are guaranteed by design.

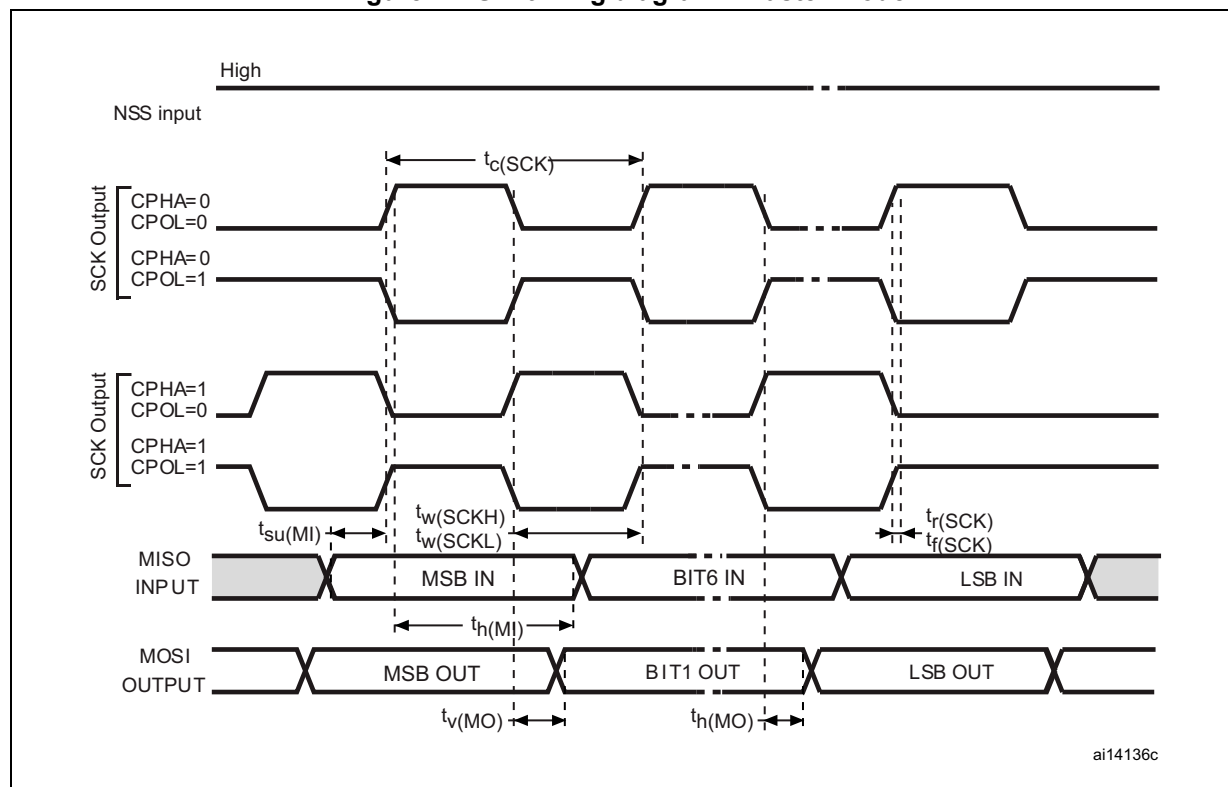
Refer to [Section 5.3.16: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 52. Characteristics of TIMx connected to the APB1 domain⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{\text{res(TIM)}}$	Timer resolution time	AHB/APB1 prescaler distinct from 1, $f_{\text{TIMxCLK}} = 84 \text{ MHz}$	1	-	t_{TIMxCLK}
			11.9	-	ns
		AHB/APB1 prescaler = 1, $f_{\text{TIMxCLK}} = 42 \text{ MHz}$	1	-	t_{TIMxCLK}
			23.8	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{\text{TIMxCLK}} = 84 \text{ MHz}$ $\text{APB1} = 42 \text{ MHz}$	0	$f_{\text{TIMxCLK}}/2$	MHz
	0		42	MHz	
Res_{TIM}	Timer resolution		-	16/32	bit
t_{COUNTER}	16-bit counter clock period when internal clock is selected		1	65536	t_{TIMxCLK}
			0.0119	780	μs
	32-bit counter clock period when internal clock is selected		1	-	t_{TIMxCLK}
			0.0119	51130563	μs
$t_{\text{MAX_COUNT}}$	Maximum possible count		-	65536×65536	t_{TIMxCLK}
			-	51.1	s

1. TIMx is used as a general term to refer to the TIM2, TIM3, TIM4, TIM5, TIM6, TIM7, and TIM12 timers.

Figure 41. SPI timing diagram - master mode



I²S interface characteristics

Unless otherwise specified, the parameters given in [Table 56](#) for the I²S interface are derived from tests performed under the ambient temperature, f_{PCLKX} frequency and V_{DD} supply voltage conditions summarized in [Table 14](#), with the following configuration:

- Output speed is set to $OSPEEDR[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5 V_{DD}$

Refer to [Section 5.3.16: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CK, SD, WS).

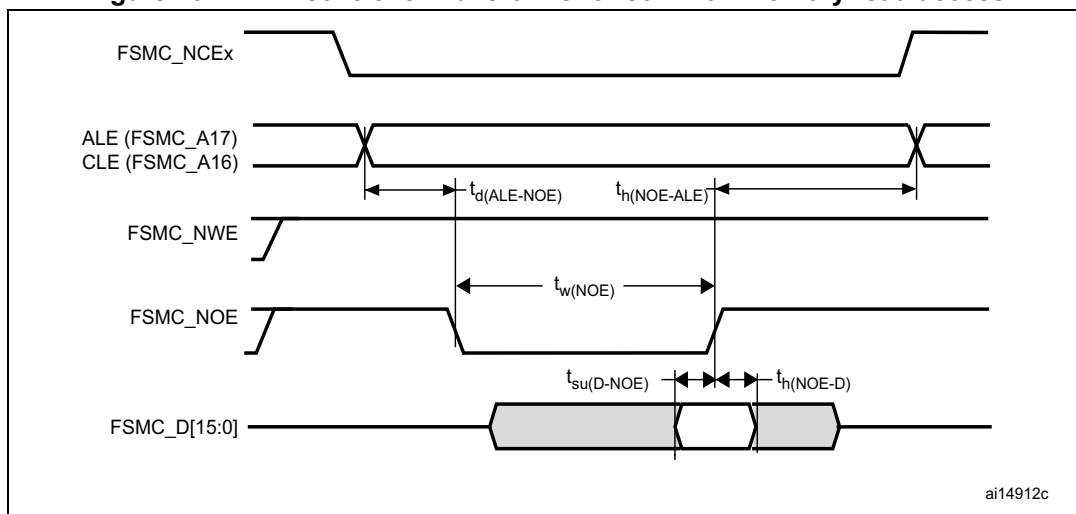
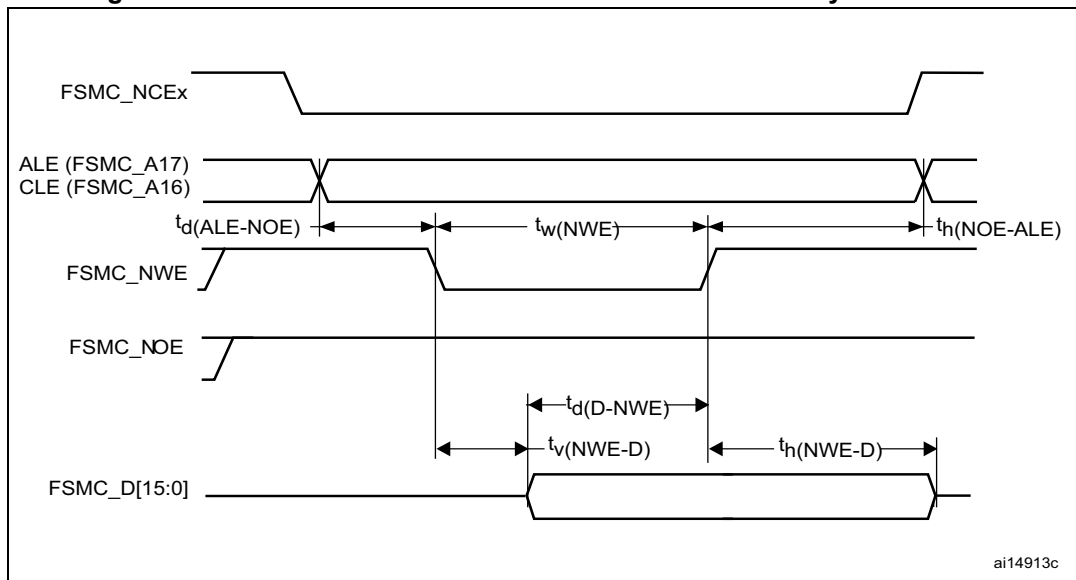
Table 56. I²S dynamic characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I ² S main clock output	-	256 x 8K	$256 \times F_S^{(2)}$	MHz
f_{CK}	I ² S clock frequency	Master data: 32 bits	-	$64 \times F_S$	MHz
		Slave data: 32 bits	-	$64 \times F_S$	
D_{CK}	I ² S clock frequency duty cycle	Slave receiver	30	70	%
$t_{V(WS)}$	WS valid time	Master mode	0	6	ns
$t_{H(WS)}$	WS hold time	Master mode	0	-	
$t_{SU(WS)}$	WS setup time	Slave mode	1	-	
$t_{H(WS)}$	WS hold time	Slave mode	0	-	
$t_{SU(SD_MR)}$	Data input setup time	Master receiver	7.5	-	
$t_{SU(SD_SR)}$		Slave receiver	2	-	
$t_{H(SD_MR)}$	Data input hold time	Master receiver	0	-	
$t_{H(SD_SR)}$		Slave receiver	0	-	
$t_{V(SD_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	27	
$t_{H(SD_ST)}$		Master transmitter (after enable edge)	-	20	
$t_{V(SD_MT)}$	Data output hold time	Master transmitter (after enable edge)	2.5	-	
$t_{H(SD_MT)}$		Master transmitter (after enable edge)	2.5	-	

1. Guaranteed by characterization.

2. The maximum value of $256 \times F_S$ is 42 MHz (APB1 maximum frequency).

Note: Refer to the I²S section of RM0090 reference manual for more details on the sampling frequency (F_S). f_{MCK} , f_{CK} , and D_{CK} values reflect only the digital peripheral behavior. The value of these parameters might be slightly impacted by the source clock accuracy. D_{CK} depends mainly on the value of ODD bit. The digital contribution leads to a minimum value of $I2SDIV / (2 \times I2SDIV + ODD)$ and a maximum value of $(I2SDIV + ODD) / (2 \times I2SDIV + ODD)$. F_S maximum value is supported for each mode/condition.

Figure 70. NAND controller waveforms for common memory read access**Figure 71. NAND controller waveforms for common memory write access****Table 85. Switching characteristics for NAND Flash read cycles⁽¹⁾**

Symbol	Parameter	Min	Max	Unit
$t_{w(NOE)}$	FSMC_NOE low width	$4T_{HCLK} - 0.5$	$4T_{HCLK} + 3$	ns
$t_{su(D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	10	-	ns
$t_h(NOE-D)$	FSMC_D[15:0] valid data after FSMC_NOE high	0	-	ns
$t_d(ALE-NOE)$	FSMC_ALE valid before FSMC_NOE low	-	$3T_{HCLK}$	ns
$t_h(NOE-ALE)$	FSMC_NWE high to FSMC_ALE invalid	$3T_{HCLK} - 2$	-	ns

1. $C_L = 30$ pF.

Table 100. Document revision history (continued)

Date	Revision	Changes
24-Jan-2012	2 (continued)	<p>Added V_{12} in Table 19: Embedded reset and power control block characteristics.</p> <p>Updated Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled) and Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM. Added Figure 25, Figure 26, and Figure 27.</p> <p>Updated Table 22: Typical and maximum current consumption in Sleep mode and removed Note 1.</p> <p>Updated Table 23: Typical and maximum current consumptions in Stop mode and Table 24: Typical and maximum current consumptions in Standby mode, Table 25: Typical and maximum current consumptions in VBAT mode, and Table 27: Switching output I/O current consumption.</p> <p>Section : On-chip peripheral current consumption: modified conditions, and updated Table 28: Peripheral current consumption and Note 2.</p> <p>Changed f_{HSE_ext} to 50 MHz and $t_{r(HSE)}/t_{f(HSE)}$ maximum value in Table 30: High-speed external user clock characteristics.</p> <p>Added $C_{in(LSE)}$ in Table 31: Low-speed external user clock characteristics.</p> <p>Updated maximum PLL input clock frequency, removed related note, and deleted jitter for MCO for RMII Ethernet typical value in Table 36: Main PLL characteristics. Updated maximum PLLI2S input clock frequency and removed related note in Table 37: PLLI2S (audio PLL) characteristics.</p> <p>Updated Section : Flash memory to specify that the devices are shipped to customers with the Flash memory erased. Updated Table 39: Flash memory characteristics, and added t_{ME} in Table 40: Flash memory programming.</p> <p>Updated Table 43: EMS characteristics, and Table 44: EMI characteristics.</p> <p>Updated Table 56: I2S dynamic characteristics</p> <p>Updated Figure 45: ULPI timing diagram and Table 62: ULPI timing.</p> <p>Added $t_{COUNTER}$ and t_{MAX_COUNT} in Table 52: Characteristics of TIMx connected to the APB1 domain and Table 53: Characteristics of TIMx connected to the APB2 domain. Updated Table 65: Dynamic characteristics: Ethernet MAC signals for RMII.</p> <p>Removed USB-IF certification in Section : USB OTG FS characteristics.</p>

Table 100. Document revision history (continued)

Date	Revision	Changes
04-Jun-2013	4 (continued)	<p>Updated Figure 6: Multi-AHB matrix.</p> <p>Updated Figure 7: Power supply supervisor interconnection with internal reset OFF</p> <p>Changed 1.2 V to V_{12} in Section : Regulator OFF</p> <p>Updated LQFP176 pin 48.</p> <p>Updated Section 1: Introduction.</p> <p>Updated Section 2: Description.</p> <p>Updated operating voltage in Table 2: STM32F415xx and STM32F417xx: features and peripheral counts.</p> <p>Updated Note 1.</p> <p>Updated Section 2.2.15: Power supply supervisor.</p> <p>Updated Section 2.2.16: Voltage regulator.</p> <p>Updated Figure 9: Regulator OFF.</p> <p>Updated Table 3: Regulator ON/OFF and internal reset ON/OFF availability.</p> <p>Updated Section 2.2.19: Low-power modes.</p> <p>Updated Section 2.2.20: VBAT operation.</p> <p>Updated Section 2.2.22: Inter-integrated circuit interface (I²C) .</p> <p>Updated pin 48 in Figure 15: STM32F41xxx LQFP176 pinout.</p> <p>Updated Table 6: Legend/abbreviations used in the pinout table.</p> <p>Updated Table 7: STM32F41xxx pin and ball definitions.</p> <p>Updated Table 14: General operating conditions.</p> <p>Updated Table 15: Limitations depending on the operating power supply range.</p> <p>Updated Section 5.3.7: Wakeup time from low-power mode.</p> <p>Updated Table 34: HSI oscillator characteristics.</p> <p>Updated Section 5.3.15: I/O current injection characteristics.</p> <p>Updated Table 48: I/O static characteristics.</p> <p>Updated Table 51: NRST pin characteristics.</p> <p>Updated Table 56: I²C characteristics.</p> <p>Updated Figure 39: I²C bus AC waveforms and measurement circuit.</p> <p>Updated Section 5.3.19: Communications interfaces.</p> <p>Updated Table 67: ADC characteristics.</p> <p>Added Table 70: Temperature sensor calibration values.</p> <p>Added Table 73: Internal reference voltage calibration values.</p> <p>Updated Section 5.3.26: FSMC characteristics.</p> <p>Updated Section 5.3.28: SD/SDIO MMC card host interface (SDIO) characteristics.</p> <p>Updated Table 23: Typical and maximum current consumptions in Stop mode.</p> <p>Updated Section : SPI interface characteristics included Table 55.</p> <p>Updated Section : I2S interface characteristics included Table 56.</p> <p>Updated Table 64: Dynamic characteristics: Eternity MAC signals for SMI.</p> <p>Updated Table 66: Dynamic characteristics: Ethernet MAC signals for MII.</p>